DP8205

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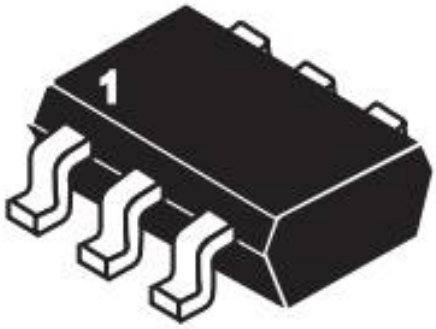
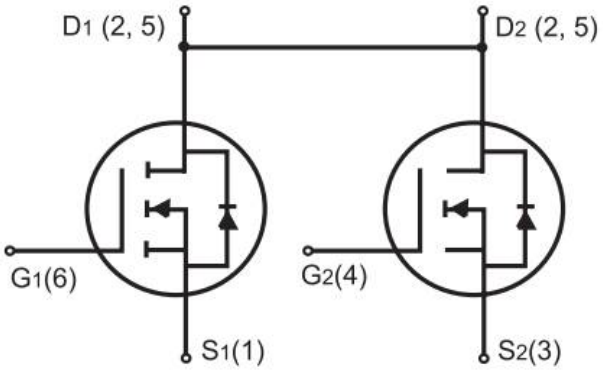
Dual N-Channel Enhancement Power MOSFET

Rev3.1

General Description	Product Summary	
DP8205 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.	V_{DS}	20 V
	I_D (at V_{GS}=4.5V)	5.0A
	$R_{DS(ON)}$ (at V_{GS} = 4.5V)	< 29mΩ
	$R_{DS(ON)}$ (at V_{GS} = 2.5V)	< 34mΩ

SOT23-6





Absolute Maximum Ratings TA=25°C unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous @ T_J=25℃	I_D	5	A
Pulsed[b]	I_{DM}	20	A
Drain-Sourse Diode Forward Current[a]	I_S	2.5	A
Maximum Power Dissipation[a]	P_D	1.25	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Parameter	Symbol	Limit	Unit
Thermal Resistance,Junction-to-Ambient [a]	$R_{\theta JA}$	100	℃/W

Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ[c]	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±12V,V_{DS}=0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	0.5	0.7	1.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_D=4.5A	-	20	29	mΩ
		V_{GS}=2.5V, I_D=3.5A	-	27	34	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=7A	-	17.7	-	S
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=8V, V_{GS}=0V, F=1.0MHz	-	802	-	pF
Output Capacitance	C_{oss}		-	153	-	pF
Reverse Transfer Capacitance	C_{rss}		-	122	-	pF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=10V, I_D=1A V_{GS}=4.5V, R_{GEN}=10Ω , R_L=10Ω	-	18	-	nS
Turn-on Rise Time	t_r		-	5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	43.8	-	nS
Turn-Off Fall Time	t_f		-	20	-	nS
Total Gate Charge	Q_g	V_{DS}=10V, I_D=4A, V_{GS}=4.5V	-	10.5	-	nC
Gate-Source Charge	Q_{gs}		-	2	-	nC
Gate-Drain Charge	Q_{gd}		-	2.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_S=1.7A	-	-	1.2	V

Notes:

a. Surface Mounted on FR4 Board ,T<10 sec ;

b. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.

c. Guaranteed by Design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

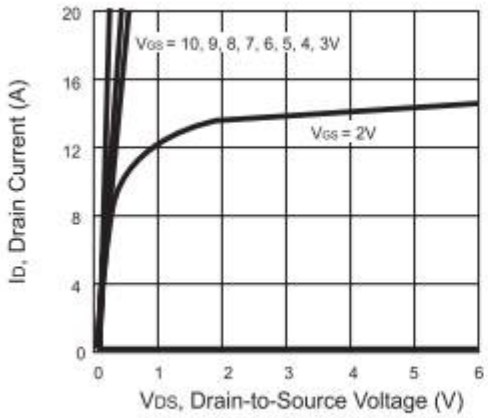


Figure 1. Output Characteristics

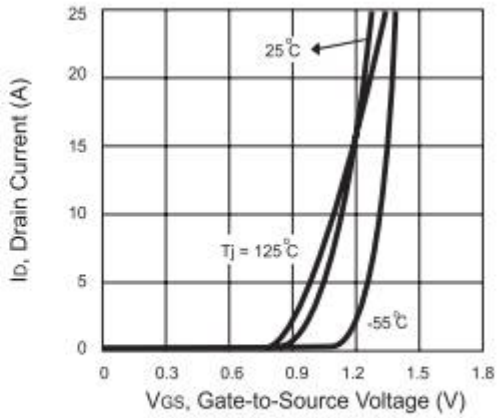


Figure 2. Thansfer Characteristics

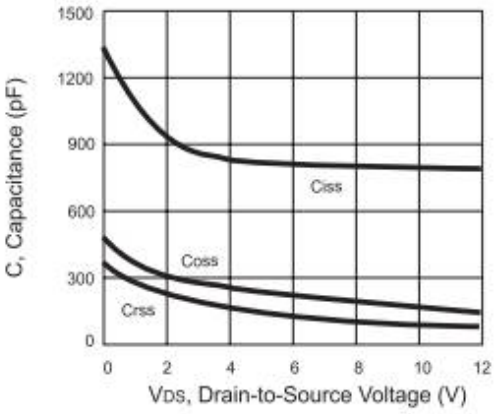


Figure 3. Capacitance

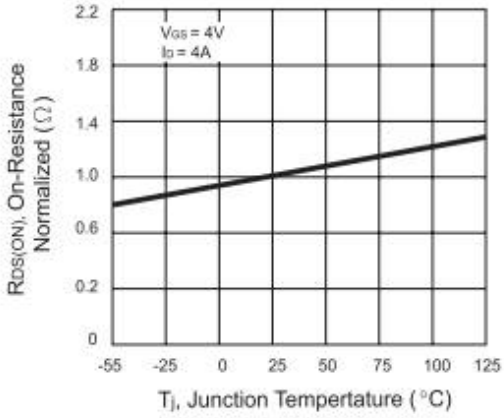


Figure 4. On-Resistance Variation with Temperature

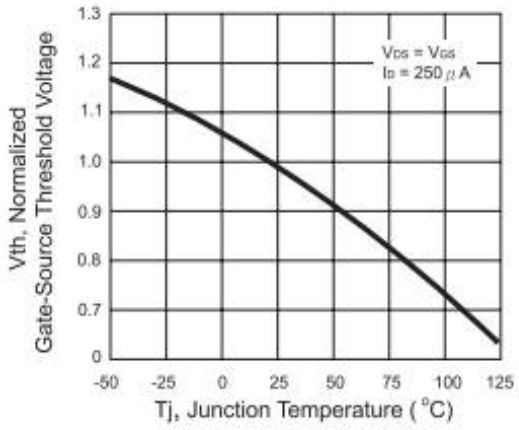


Figure 5. Gate Threshold Variation with Temperature

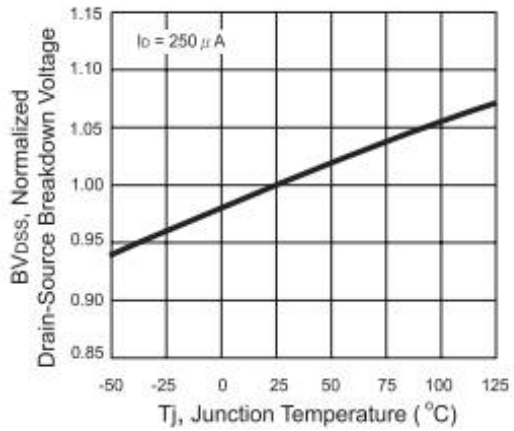


Figure 6. Breakdown Voltage Variation with Temperature

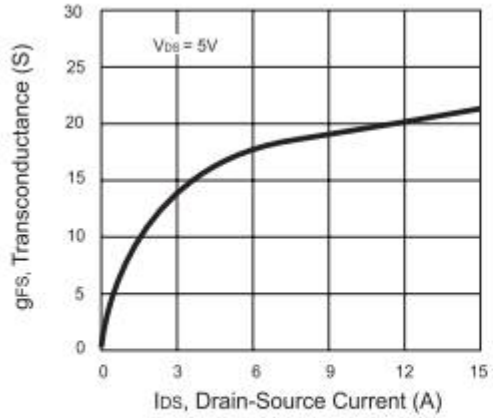


Figure 7. Transconductance Variation with Drain Current

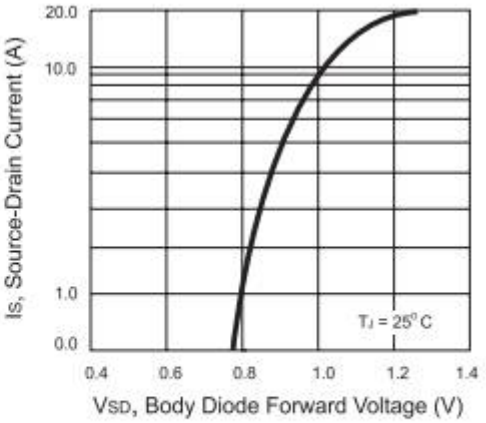


Figure 8. Body Diode Forward Voltage Variation with Source Current

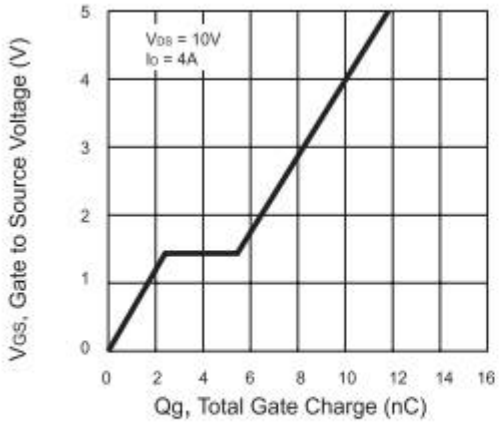


Figure 9. Gate Charge

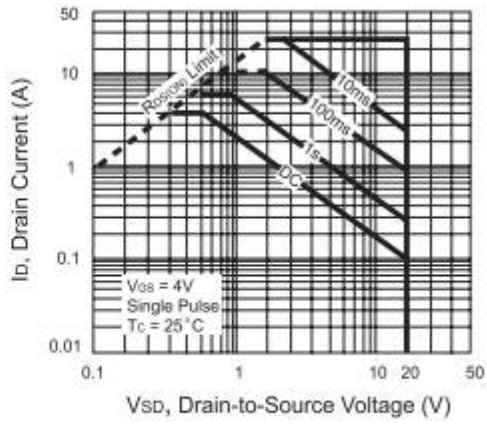


Figure 10. Maximum Safe Operating Area

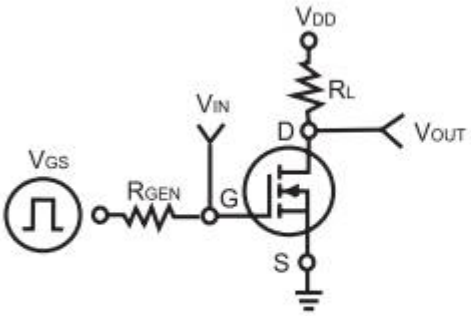


Figure 11. Switching Test Circuit

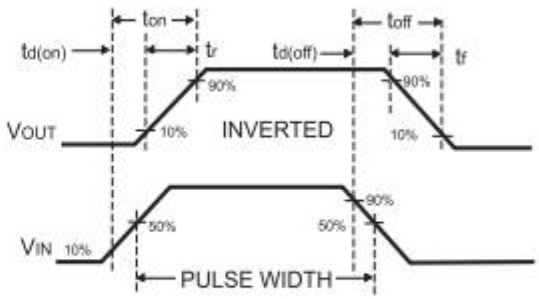


Figure 12. Switching Waveforms

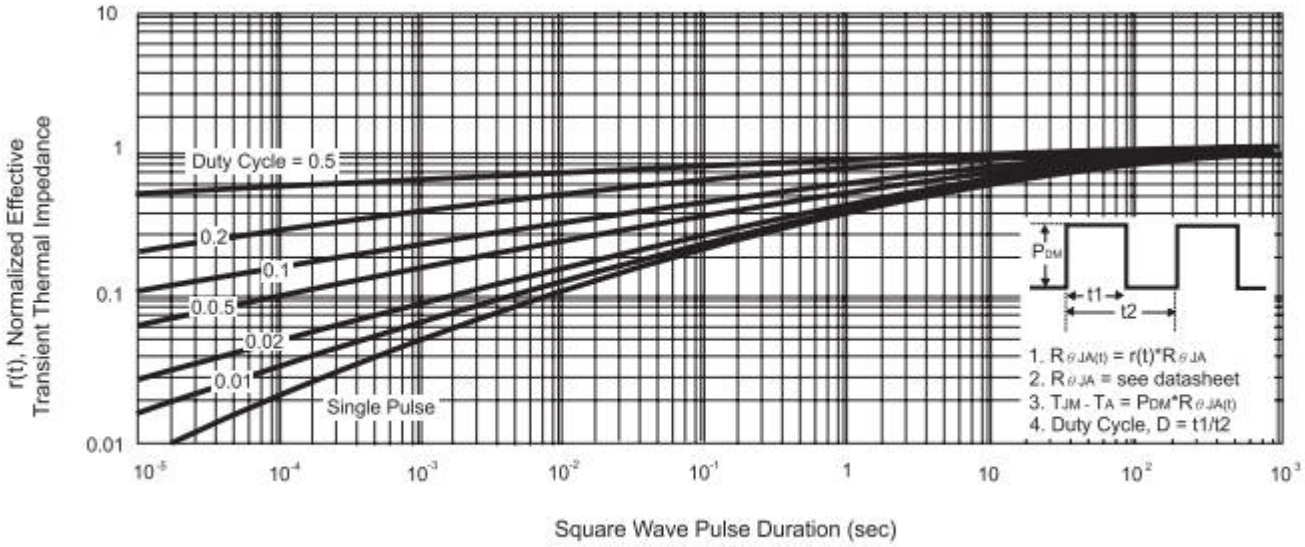
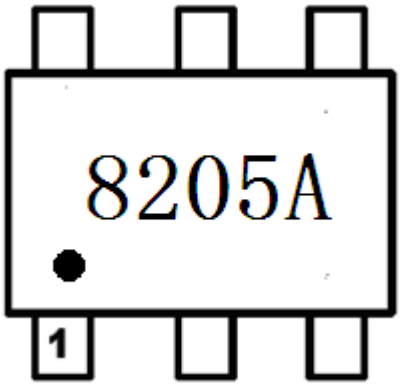
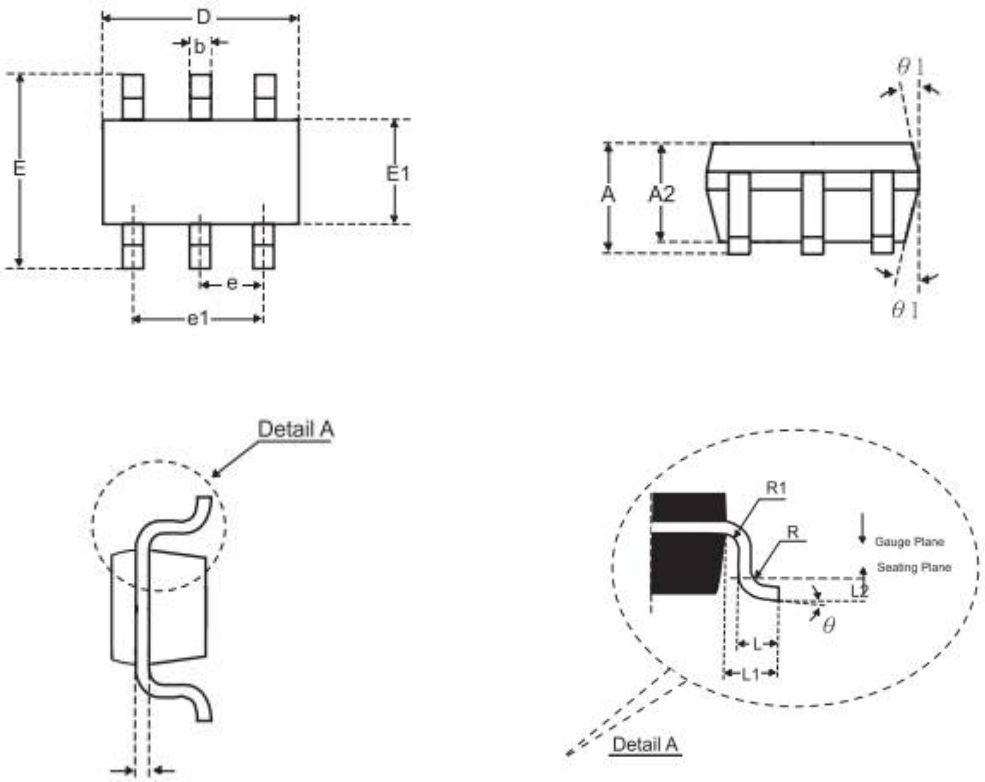


Figure 13. Normalized Thermal Transient Impedance Curve

MARKING DESCRIPSION **SOT23-6**



Package Outline Dimensions SOT23-6



SYMBOLS	MILLIMETERS		
	Min.	Nom.	Max.
A	-	-	1.45
A2	0.90	0.15	1.30
b	0.30	-	0.50
c	0.08	-	0.22
D	2.70	2.90	3.10
E	2.50	2.80	3.10
E1	1.50	1.60	1.70
e	0.95 BSC		
e1	1.90 BSC		
L	0.30	0.45	0.60
L1	0.60 BSC		
L2	0.20 BSC		
R	0.10	-	-
R1	0.10	-	0.25
θ	0°	4°	8°
θ1	0°	10°	15°